

## IN THE CLAIMS

Claims 1-8 have previously been cancelled without prejudice.

Claims 11-15 have previously been cancelled without prejudice as being drawn to a non-elected invention.

Please enter the pending claims as follows:

1. – 8. (Cancelled)

9. (Previously Presented) An apparatus comprising:

- a platen;

- a polishing pad disposed over said platen, said polishing pad having properties that may be changed to optimize polish rate and polish selectivity for different materials, said properties comprising: hardness, stiffness, porosity, abrasiveness, and absorbance;

- a segmented cathode disposed between said platen and a rear surface of said polishing pad;

- a slurry disposed on said polishing pad;

- a wafer disposed on said polishing pad and said slurry;

- a wafer carrier to hold said wafer;

a segmented anode disposed between a rear surface of said wafer and said wafer carrier, said segmented anode being partitioned into small components that may be adjusted separately;

a power supply to apply a voltage between said segmented cathode and said segmented anode; and

a computer to vary said voltage.

10. (Previously Presented) The apparatus of claim 9 wherein said wafer comprises a continuous and conductive surface layer.

11. – 15. (Cancelled)

16. (Previously Presented) The apparatus of claim 9 wherein said computer optimizes polishing rates for different materials on said wafer by varying said voltage.

17. (Previously Presented) The apparatus of claim 9 wherein said computer varies said voltage as a function of time.

18. (Previously Presented) The apparatus of claim 9 wherein said computer varies said voltage as a function of temperature.

19. (Previously Presented) The apparatus of claim 9 wherein said computer varies said voltage as a function of process parameter.

20. (Previously Presented) The apparatus of claim 19 wherein said process parameter comprises slurry flowrate.

21. (Previously Presented) The apparatus of claim 9 wherein said computer varies said voltage as a function of tool parameter.

22. (Previously Presented) The apparatus of claim 21 wherein said tool parameter comprises speed of rotation of said platen.

23. (Previously Presented) The apparatus of claim 21 wherein said tool parameter comprises speed of rotation of said wafer carrier.

24. (Previously Presented) The apparatus of claim 9 wherein said computer comprises feedforward control of an electrochemical process.

25. (Previously Presented) The apparatus of claim 9 wherein said computer comprises feedback control of an electrochemical process.

26. (Previously Presented) The apparatus of claim 9 wherein said computer comprises proportional control of said voltage.

27. (Previously Presented) The apparatus of claim 9 wherein said computer comprises differential control of said voltage.

28. (Previously Presented) The apparatus of claim 9 wherein said computer comprises integral control of said voltage.